

NPN TRANSISTOR

8050S

0.5A



TO-92

- Power Dissipation: 0.625W
- Collector Current: 0.5A
- Collector-Base Voltage: 45V

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS (Ta=25)

PARAMETERS	SYMBOL	MIN	TYP	MAX	UNIT	CONDITION
Collector-Emitter Breakdown Voltage	BV _{ceo}	25			V	I _c =0.1mA
Collector-Base Breakdown Voltage	BV _{cb0}	45			V	I _c =100μA
Emitter-Base Breakdown Voltage	BV _{eb0}	5			V	I _e =100 μ A
Collector-Base Leakage	I _{cbo}			0.1	μA	V _{cb} =40V
Collector-Emitter Leakage	I _{ceo}			0.1	μA	V _{ce} =20V
Emitter-Base Leakage	I _{ebo}			0.1	μA	V _{eb} =5V
Collector-Emitter Saturation Voltage	V _{ce(sat)}			0.6	V	I _c =500mA, I _b =50mA
Base-Emitter Saturation Voltage	V _{be(sat)}			1.2	V	I _c =500mA, I _b =50mA
DC Current Gain	H _{fe1} H _{fe2}	85 50		300		V _{ce} =1V, I _c =50mA V _{ce} =1V, I _c =500mA
Collector Current	I _c			0.5	A	
Peak Collector Current	I _{cp}			8	A(Pulse)	
Current Gain Bandwidth	f _r	150			MHz	V _{cb} =6V, I _c =20mA
Output Capacitance	C _{ob}			32	pF	V _{cb} =20V, I _e =0, f=1MHz
Power Dissipation	P _c			0.625	W	
Junction Temperature	T _j			150		
Storage Temperature	T _{stg}	-55		150		

Hfe1 Classification

Rank	B	C	D
Range	85-160	120-200	160-300



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